JMSH04060G3L

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% Vds Tested
- Halogen-free; RoHS-compliant

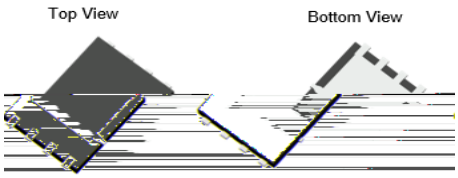
Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

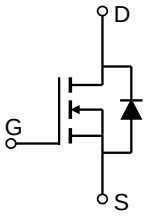
Parameters	Value	Unit
V_{DSS}	40	V
$V_{GS(th)\_Typ}$	2.8	V
I_D(@V_{GS}=10V)	87	A
$R_{DS(ON)\_Typ}$(@V_{GS}=10V	4.8	mΩ

RoHS



PDFN5X6-8L

Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH04060G3L-13	SH040603L	1	Tape&Reel	PDFN5x6-8L	5000	50000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		40	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	87	A
		T_C = 100°C	62	
I_{DM}	Pulsed Drain Current [1]		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy [2]		106	mJ
P_D	Power Dissipation	T_C = 25°C	83	W
		T_C = 100°C	42	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
R	Thermal Resistance, Junction to Ambient[3]	45	°C/W
R	Thermal Resistance, Junction to Case	1.8	

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 32V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	2.8	4.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 20A	-	4.8	6.0	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	1.6	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 20V, f = 1MHz	-	1068	1450	pF
C_{oss}	Output Capacitance		-	355	480	pF
C_{rss}	Reverse Transfer Capacitance		-	10	20	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 20V, I_D = 20A	-	15	-	nC
Q_{gs}	Gate Source Charge		-	6	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 20V I_D= 20A, R_{GEN} = 3Ω	-	10	-	ns
t_r	Turn-On Rise Time		-	28	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	15	-	ns
t_f	Turn-Off Fall Time		-	3	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	87	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	350	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	11	22	32	ns
Qrr	Body Diode Reverse Recovery Charge		-	12	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25C, V_{DD}=20V, V_{GS}=10V, R_G=25ohm, L=3mH, I_{AS}=8.4A, V_{DD}=0V during time in avalanche.

3. R is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.

4. Pulse Test: Pulse Width≤ ≤0.5%.

Typical Performance Characteristics

Figure 1: Power De-rating

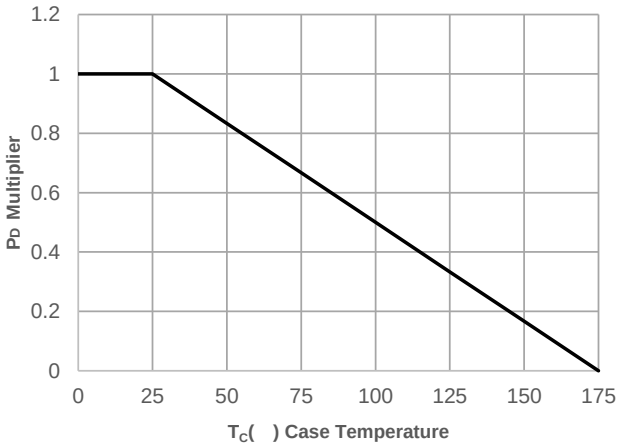
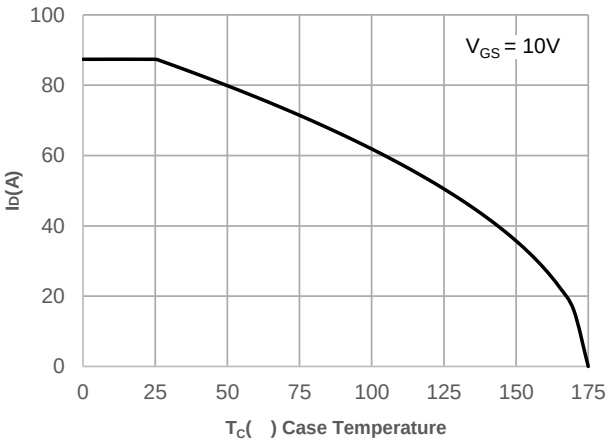
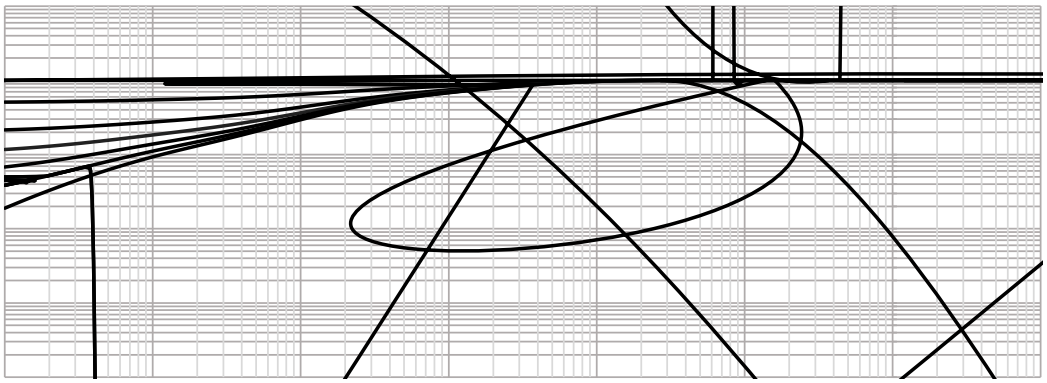
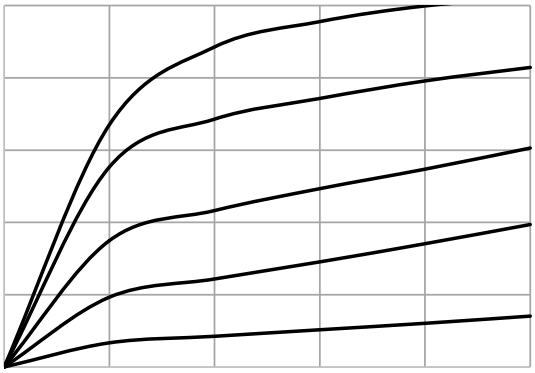


Figure 2: Current De-rating





Typical Performance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown Voltage vs. Junction Temperature

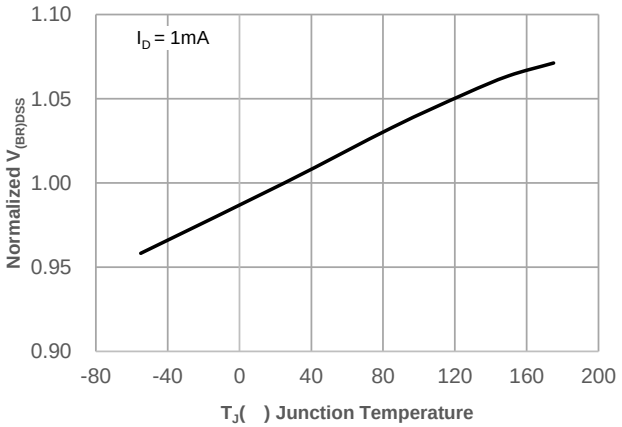


Figure 12: Normalized on Resistance vs. Junction Temperature

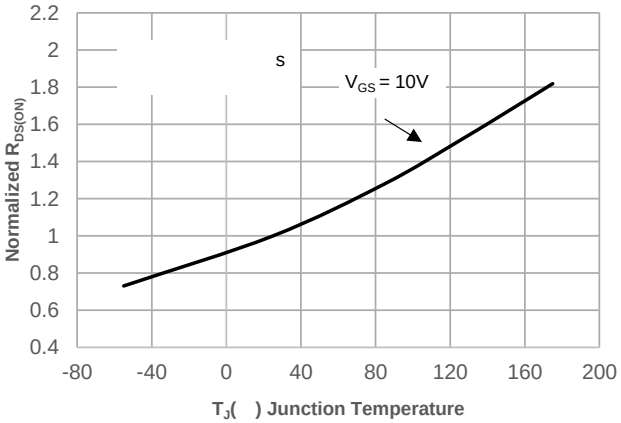


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

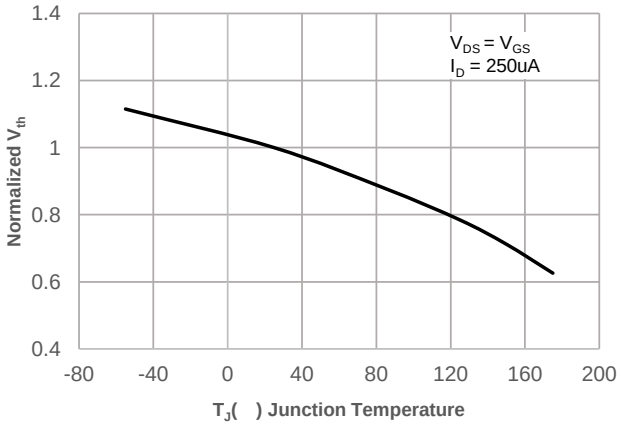


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

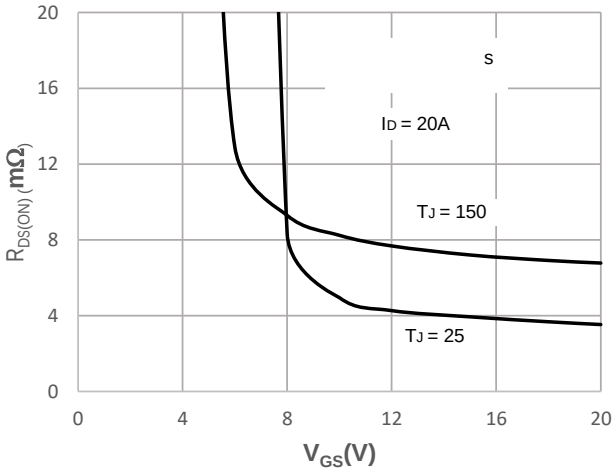
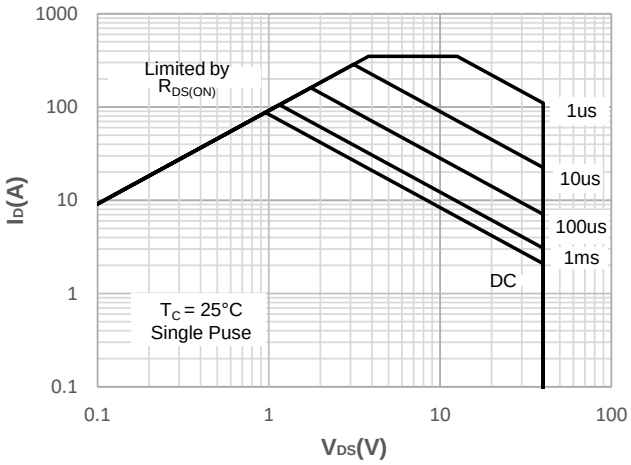


Figure 15: Maximum Safe Operating Area



Test Circuit

Figure 1: Gate Charge Test Circuit & Waveform

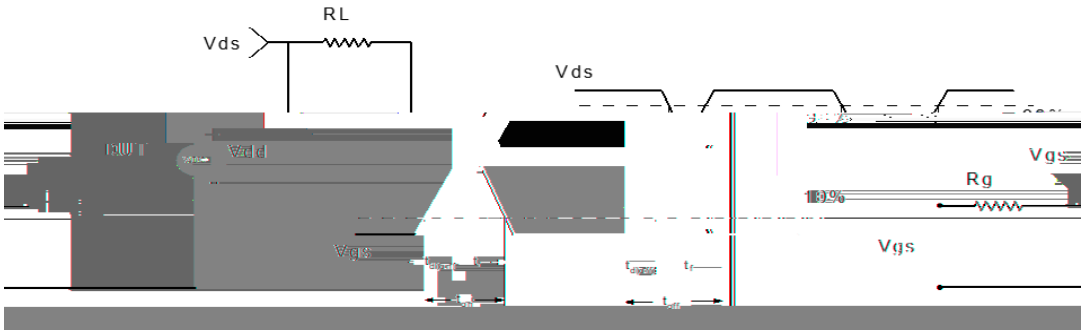


Figure 2: Resistive Switching Test Circuit & Waveform

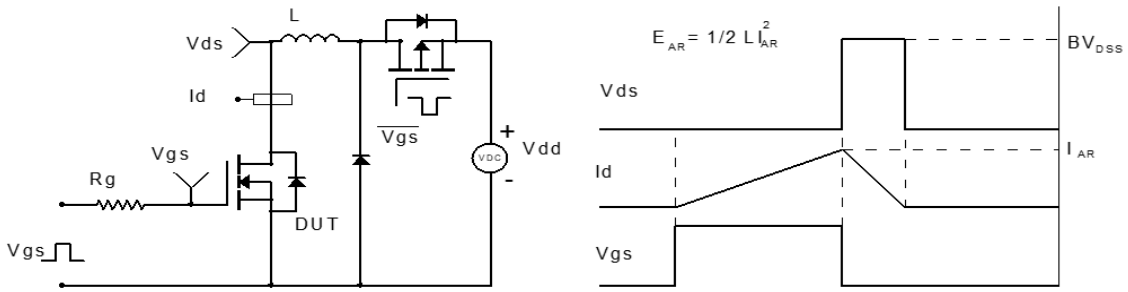


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

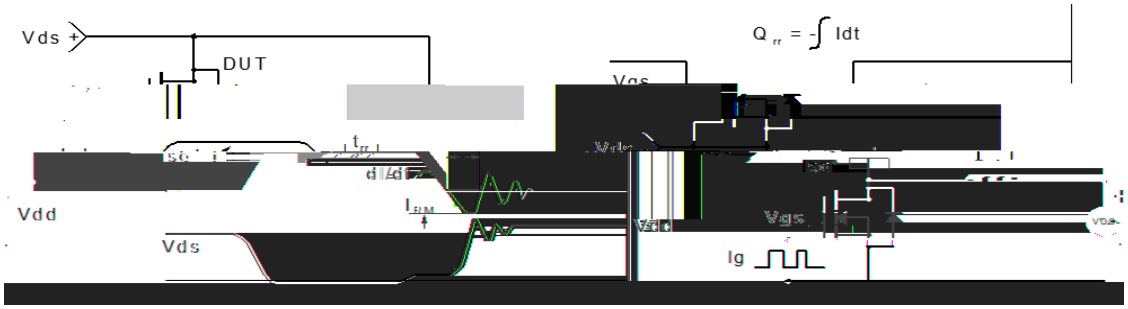
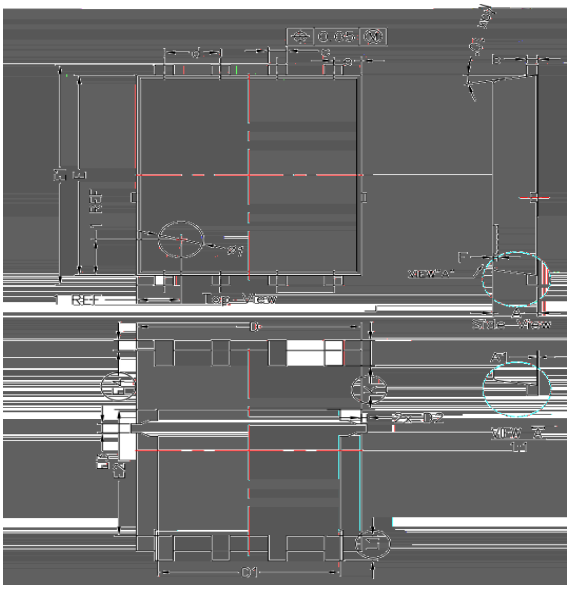


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN5X6-8L)



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
*A	0.900	1.000	1.150	0.035	0.039	0.045
A1	0.000	---	0.050	0.000	---	0.002
b	0.246	0.254	0.350	0.010	0.010	0.014
c	0.203REF			0.008REF		
e	1.27BSC			0.050BSC		
*D	4.950	5.050	5.150	0.195	0.199	0.203
D1	4.800	4.100	4.200	0.157	0.161	0.165
*D2	0.125REF			0.005REF		
E	5.950	6.050	6.150	0.234	0.238	0.242
*E	5.500	5.600	5.700	0.217	0.220	0.224
E1	3.950	4.050	4.150	0.156	0.159	0.163
E2	3.425	3.525	3.625	0.135	0.138	0.143
*E4	0.273REF			0.011REF		
F	---	---	0.100	---	---	0.004
*L	0.500	0.600	0.700	0.020	0.024	0.028
L1	0.600	0.700	0.800	0.024	0.028	0.031
K	1.225REF			0.048REF		
R	0.20	0.25	0.30	0.008	0.010	0.012
R1	0.20	0.25	0.30	0.008	0.010	0.012
R2	0.20	0.25	0.30	0.008	0.010	0.012
θ	0°	---	12°	0°	---	12°
θ1	10°	12°	14°	10°	12°	14°
θ2	10°	12°	14°	10°	12°	14°

Recommended Soldering Footprint